

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.7	C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	C

Electrical Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 10A$				
		$V_{GS} = 4.5V, I_D = 5A$				
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 10A$				
Source-drain voltage	V_{SD}	$I_S = 10A$				

Electrical Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	890	-	pF
Output capacitance	C_{oss}		-	423	-	
Reverse transfer capacitance	C_{rss}		-	8.1	-	

Gate Charge characteristics ($T_a = 25$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	11	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	2.0	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	1.2	-	

Note: ;



Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

Fig.4 Typical output Characteristics

Fig.5 Threshold Voltage V.S Junction Temperature Fig.6 Resistance V.S Drain Current

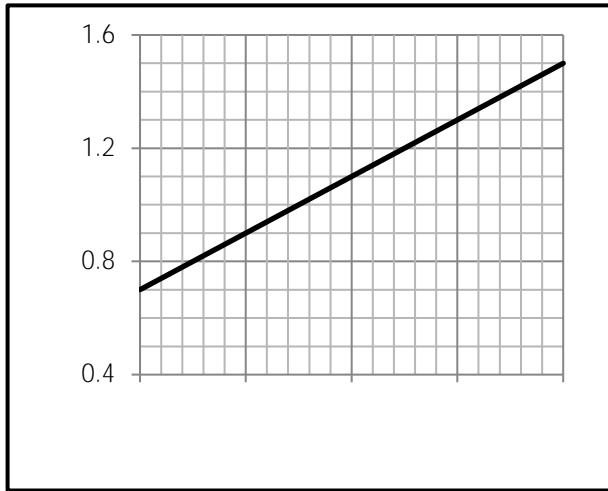


Fig.9 Switching Time Measurement Circuit

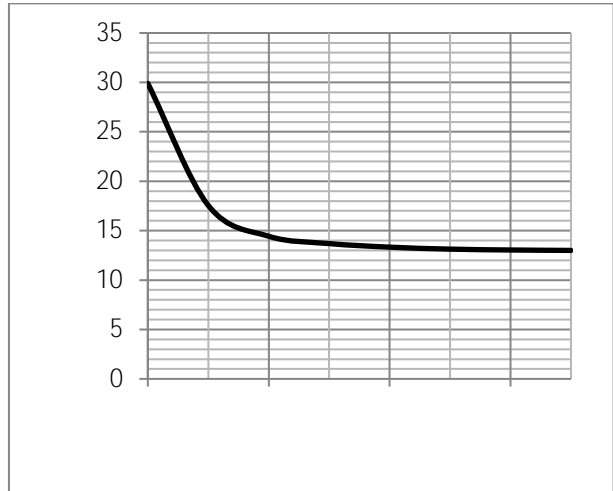


Fig.10 Gate Charge Waveform

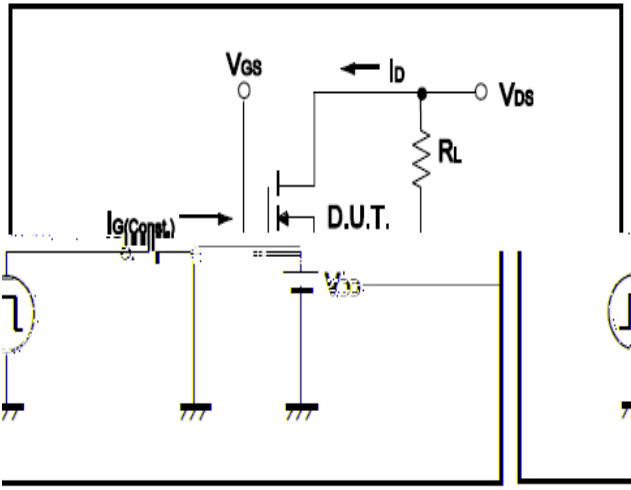


Fig.11 Switching Time Measurement Circuit

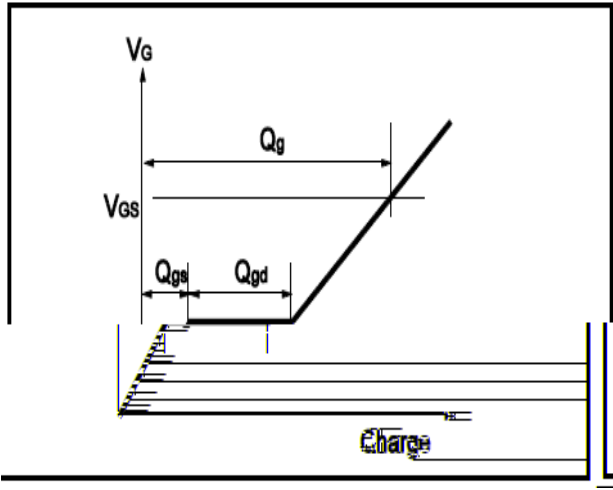


Fig.12 Gate Charge Waveform

